L Number	Hits	Search Text	DB	Time stamp
-	4	(("6069485") or ("5904490")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:22
-	2	("5610104").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 18:40
-	23044	transistor near2 structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:22
-	11021	transistor adj structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:23
-	6868	(transistor adj structure) and 257/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:23
-	118	(base with gate with drain) with insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:24
-	13	((transistor adj structure) and 257/$.ccls.) and ((base with gate with drain) with insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:36
-	350	324/769.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 11:36
-	4	324/769.ccls. and (determin$4 near5 capacitance) same (gate and source and drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 12:54
-	4	("5304925" | "5493231" | "5493238" | "5519336").PN.	USPAT	2003/12/04 11:45
-	3	("5194923" | "5268318" | "5600578").PN.	USPAT	2003/12/04 12:54
-	371	(determin$4 near5 capacitance) same (gate and source and drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 13:05
-	14	((determin$4 near5 capacitance) same (gate and source and drain)) and measur$4 near5 characteristic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 12:55
-	4	((determin$4 near5 capacitance) same (gate and source and drain)) and 324/766-769.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 13:01
-	356	((determin$4 near5 capacitance) same (gate and source and drain)) and (transistor or integrated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 13:06

-	95	(((determin$4 near5 capacitance) same (gate and source and drain)) and (transistor or integrated)) and (bias adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 13:37
-	12	(measur$4 near5 capacitance near5 (transistor or (integrated adj circuit))) and 324/766-769.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 13:39
-	186	measur$4 near5 capacitance near5 (transistor or (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 18:38
-	0	"406085019".PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 16:13
-	9943	Aizawa.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 16:14
-	0	Aizawa.inv. and "406085019"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 16:14
-	1	Aizawa.inv. and "06085019"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 16:17
-	2	"6207477".PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 16:17
-	186	measur$4 near5 capacitance near5 (transistor or (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 18:38
-	781	measur$4 near5 capacitance same (transistor or (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 11:29
-	52	(measur$4 near5 capacitance same (transistor or (integrated adj circuit))) and (word or bit) adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/04 18:39
-	2261	memory adj array adj2 cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 11:30
-	781	measur$4 near5 capacitance same (transistor or (integrated adj circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 11:29
-	0	(memory adj array adj2 cell) and (measur$4 near5 capacitance same (transistor or (integrated adj circuit)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 11:29

-	78	(memory adj array adj2 cell) and (measur$4 or determin$4) with capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 11:34
-	50	((memory adj array adj2 cell) and (measur$4 or determin$4) with capacitance) and (word adj line) and (bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 13:37
-	17	(("3,753,373" or "4,473,796" or "4,498,044" or "5,416,470" or "5,701,101" or "5,808,516" or "5,886,529" or "5,986,456" or "6,054,867")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/05 13:38